

N-channel TrenchMOS standard level FET

Rev. 02 — 16 June 2010

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

1.3 Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching

Suitable for standard level gate drive sources

Motors, lamps and solenoids

1.4 Quick reference data

Table 1.	Quick reference da	ta				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	-	55	V
I _D	drain current	V _{GS} = 10 V; T _{sp} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	5.5	A
P _{tot}	total power dissipation	T _{sp} = 25 °C; see <u>Figure 2</u>	-	-	8	W
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A};$ $T_j = 150 \text{ °C};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	278	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A};$ $T_j = 25 \text{ °C};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	128	150	mΩ
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 5 \text{ A}; V_{sup} \leq 55 \text{ V}; \\ R_{GS} &= 50 \Omega; V_{GS} = 10 \text{ V}; \\ T_{j(\text{init})} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $	-	-	25	mJ

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain		
3	S	source		
4	D	drain		G-CI-CI-CI-CI-CI-CI-CI-CI-CI-CI-CI-CI-CI-
				mbb076 S
			SOT223 (SC-73)	

3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
BUK78150-55A	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223		

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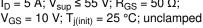
Limiting values 4.

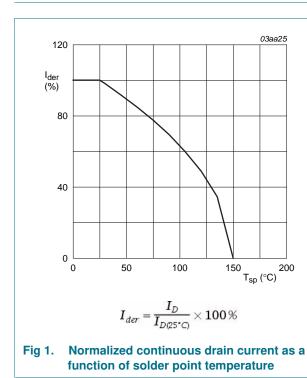
Limiting values Table 4.

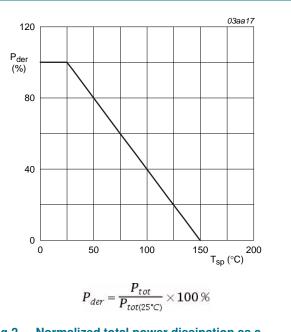
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	-	55	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	-	55	V
V _{GS}	gate-source voltage		-20	-	20	V
I _D	drain current	$T_{sp} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 3}};$	-	-	5.5	A
		T_{sp} = 100 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	-	3.8	А
I _{DM}	peak drain current	T_{sp} = 25 °C; $t_p \le 10 \ \mu s$; pulsed; see Figure 3	-	-	22	A
P _{tot}	total power dissipation	T _{sp} = 25 °C; see <u>Figure 2</u>	-	-	8	W
T _{stg}	storage temperature		-55	-	150	°C
Tj	junction temperature		-55	-	150	°C
Source-drai	in diode					
ls	source current	T _{sp} = 25 °C	-	-	5.5	А
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{sp} = 25 \ ^{\circ}C$	-	-	22	А
Avalanche I	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source	$I_D = 5$ A; $V_{sup} ≤ 55$ V; $R_{GS} = 50$ Ω; Voc = 10 V: Tiggin = 25 °C: upclamped	-	-	25	mJ

drain-source avalanche energy



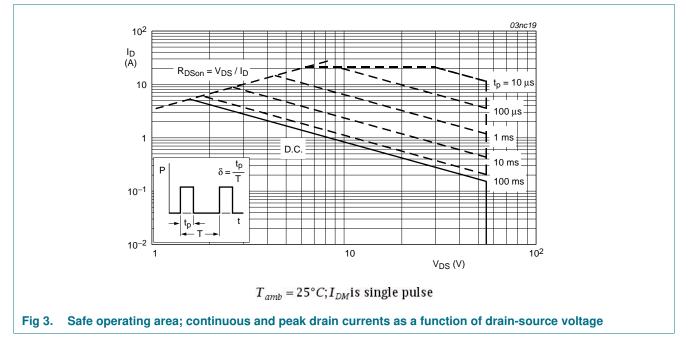






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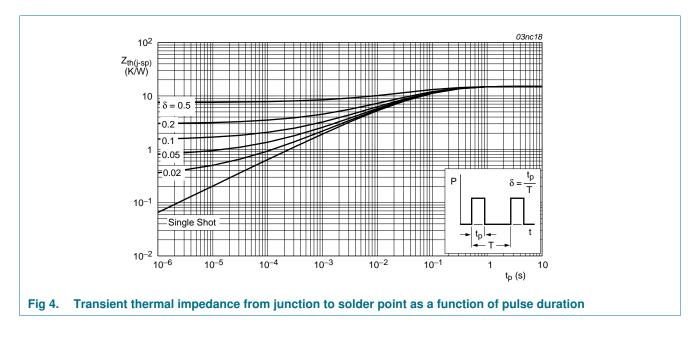
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5. Thermal characteristics

Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Mi	n Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	15	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	see <u>Figure 4</u>	-	70	-	K/W



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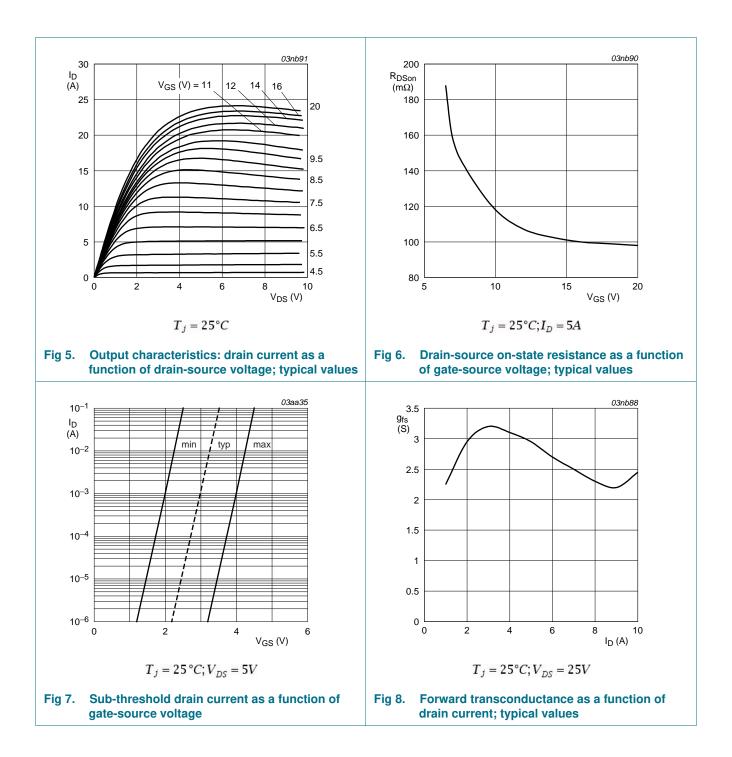
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6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see Figure 11	2	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 150 °C; see <u>Figure 11</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 11	-	-	4.4	V
I _{DSS}	drain leakage current	V _{DS} = 55 V; V _{GS} = 0 V; T _j = 150 °C	-	-	500	μA
		V _{DS} = 55 V; V _{GS} = 0 V; T _j = 25 °C	-	0.05	10	μA
I _{GSS}	gate leakage current	V _{DS} = 0 V; V _{GS} = 20 V; T _j = 25 °C	-	2	100	nA
		$V_{DS} = 0 V; V_{GS} = -20 V; T_j = 25 °C$	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 5 A; T_j = 150 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	278	mΩ
		V_{GS} = 10 V; I_D = 5 A; T_j = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	128	150	mΩ
Dynamic	characteristics					
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	170	230	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	54	65	pF
C _{rss}	reverse transfer capacitance		-	37	52	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 2.7 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	3	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \ \Omega; \ T_j = 25 \ ^{\circ}C$	-	26	-	ns
t _{d(off)}	turn-off delay time		-	8	-	ns
t _f	fall time		-	10	-	ns
Source-d	rain diode					
V_{SD}	source-drain voltage	I _S = 5 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 15</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 10 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$	-	32	-	ns
Q _r	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	50	-	nC

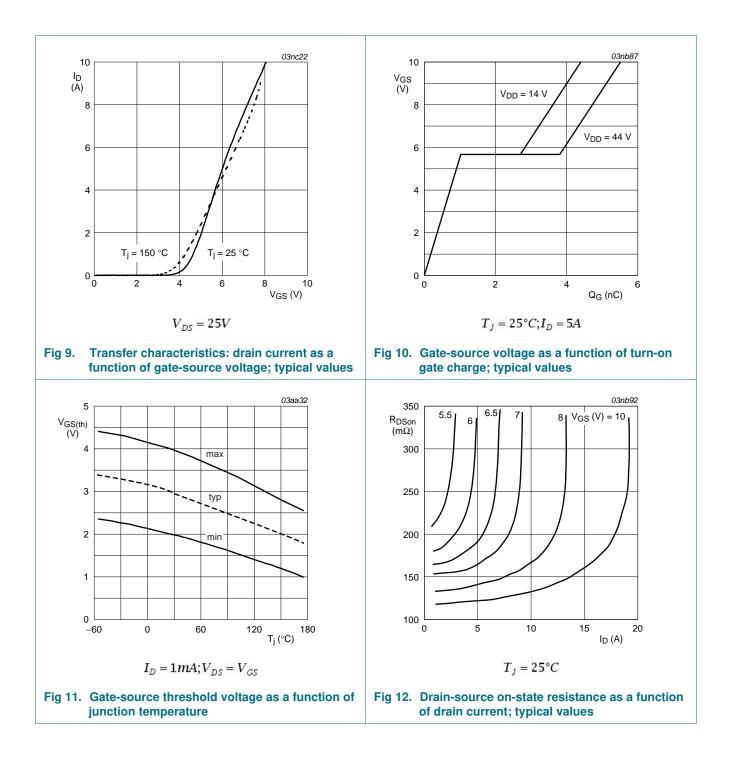
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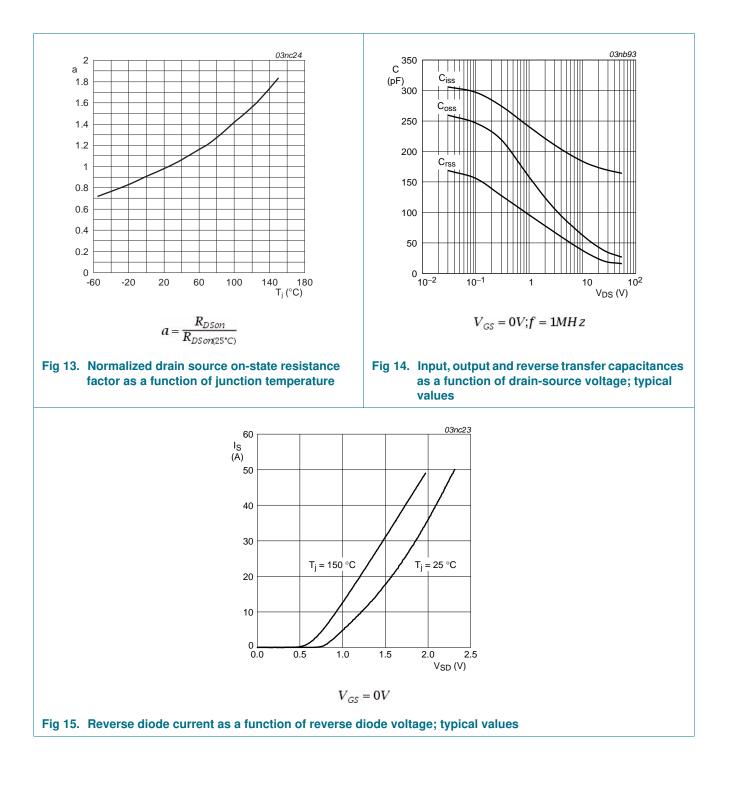
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7. Package outline

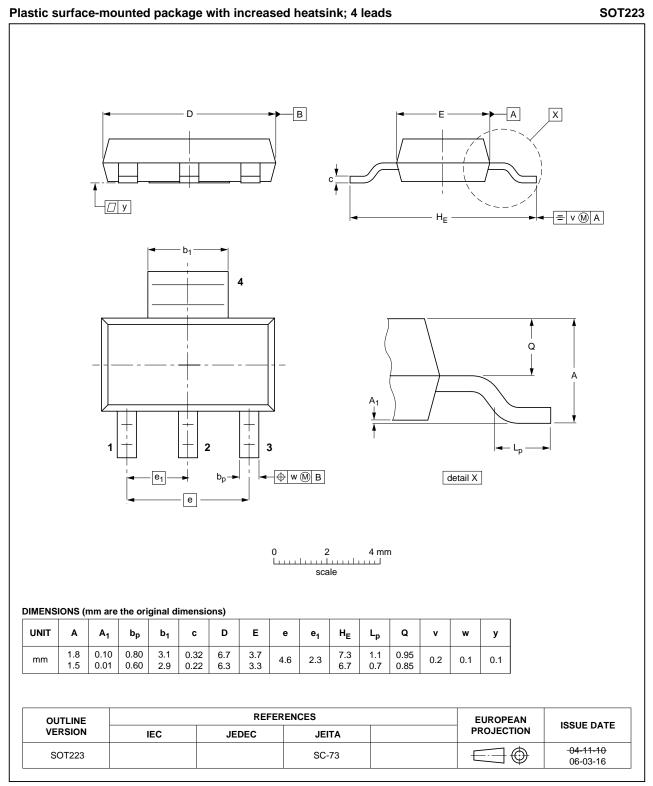


Fig 16. Package outline SOT223 (SC-73)

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8. Revision history

Table 7. Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK78150-55A v.2	20100616	Product data sheet	-	BUK78150-55A v.1
Modifications:	of NXP Se	miconductors	en redesigned to comply ne new company name w	with the new identity guidelines here appropriate.
BUK78150-55A v.1 (9397 750 07738)	20010130	Product Specification	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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